

# Plastic Medium Power Silicon NPN Transistor

... designed for use in 5.0 to 10 Watt audio amplifiers and drivers utilizing complementary or quasi complementary circuits.

- DC Current Gain —  $h_{FE} = 40$  (Min) @  $I_C = 0.15$  Adc
- BD179 is complementary with BD180

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	80	Vdc
Collector–Base Voltage	$V_{CBO}$	80	Vdc
Emitter–Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current	$I_C$	3.0	Adc
Base Current	$I_B$	1.0	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	30 240	Watts mw/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$\theta_{JC}$	4.16	$^\circ\text{C/W}$

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

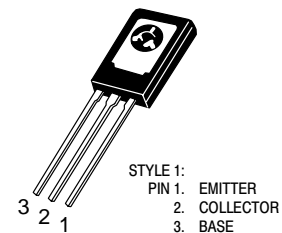
Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Sustaining Voltage* ( $I_C = 0.1$ Adc, $I_B = 0$ )	$V_{(BR)CEO}$	80	—	Vdc
Collector Cutoff Current ( $V_{CB} = 80$ Vdc, $I_E = 0$ )	$I_{CBO}$	—	0.1	mAdc
Emitter Cutoff Current ( $V_{BE} = 5.0$ Vdc, $I_C = 0$ )	$I_{EBO}$	—	1.0	mAdc
DC Current Gain ( $I_C = 0.15$ A, $V_{CE} = 2.0$ V) BD179–10 ( $I_C = 1.0$ A, $V_{CE} = 2.0$ V) ALL	$h_{FE}$	63 15	160 —	
Collector–Emitter Saturation Voltage* ( $I_C = 1.0$ Adc, $I_B = 0.1$ Adc)	$V_{CE(sat)}$	—	0.8	Vdc
Base–Emitter On Voltage* ( $I_C = 1.0$ Adc, $V_{CE} = 2.0$ Vdc)	$V_{BE(on)}$	—	1.3	Vdc
Current–Gain – Bandwidth Product ( $I_C = 250$ mAdc, $V_{CE} = 10$ Vdc, $f = 1.0$ MHz)	$f_T$	3.0	—	MHz

\*Pulse Test: Pulse Width  $\leq 300$  As, Duty Cycle  $\leq 2.0\%$ .

**BD179**  
**BD179-10**

**3.0 AMPERES**  
**POWER TRANSISTORS**  
**NPN SILICON**  
**80 VOLTS**  
**30 WATTS**

\*ON Semiconductor Preferred Device



**CASE 77–09**  
**TO–225AA TYPE**

# BD179 BD179-10

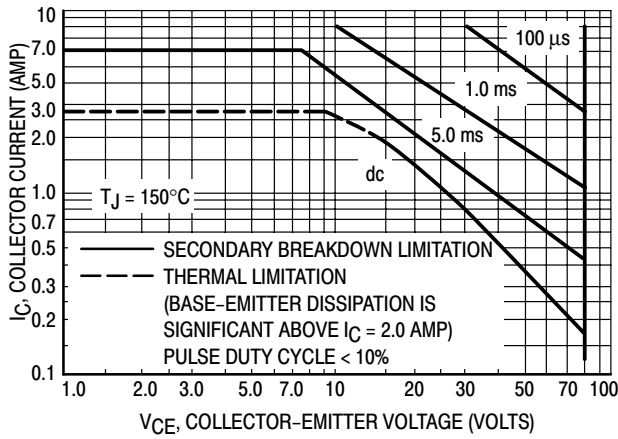


Figure 1. Active Region Safe Operating Area

The Safe Operating Area Curves indicate  $I_C - V_{CE}$  limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below the maximum  $T_J$ , power-temperature derating must be observed for both steady state and pulse power conditions.

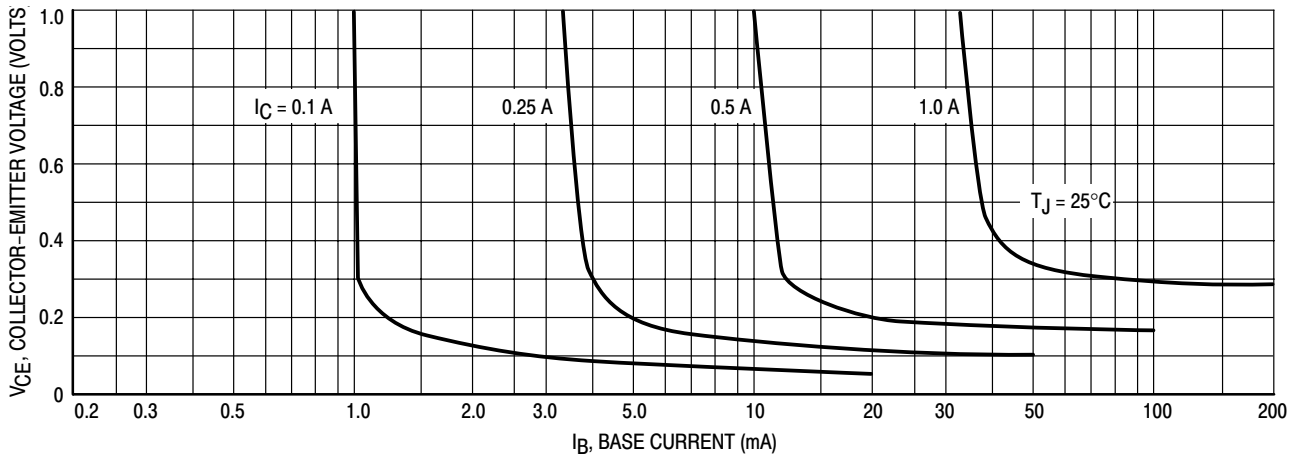


Figure 2. Collector Saturation Region

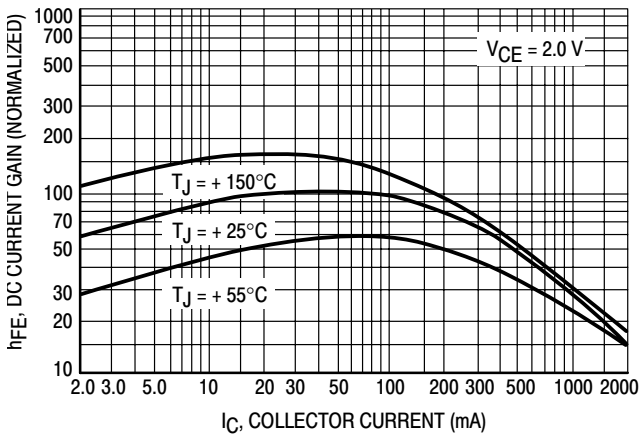


Figure 3. Current Gain

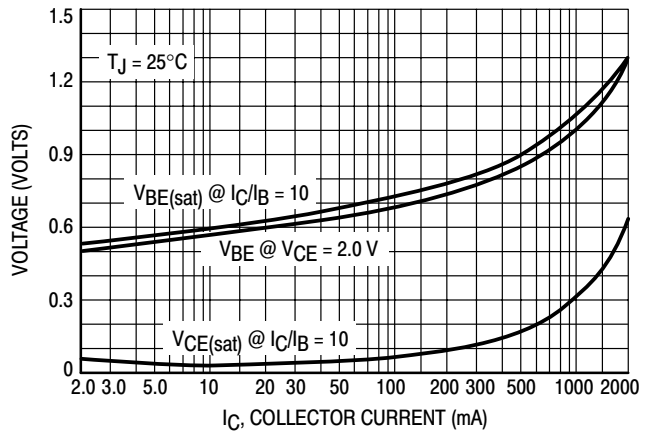
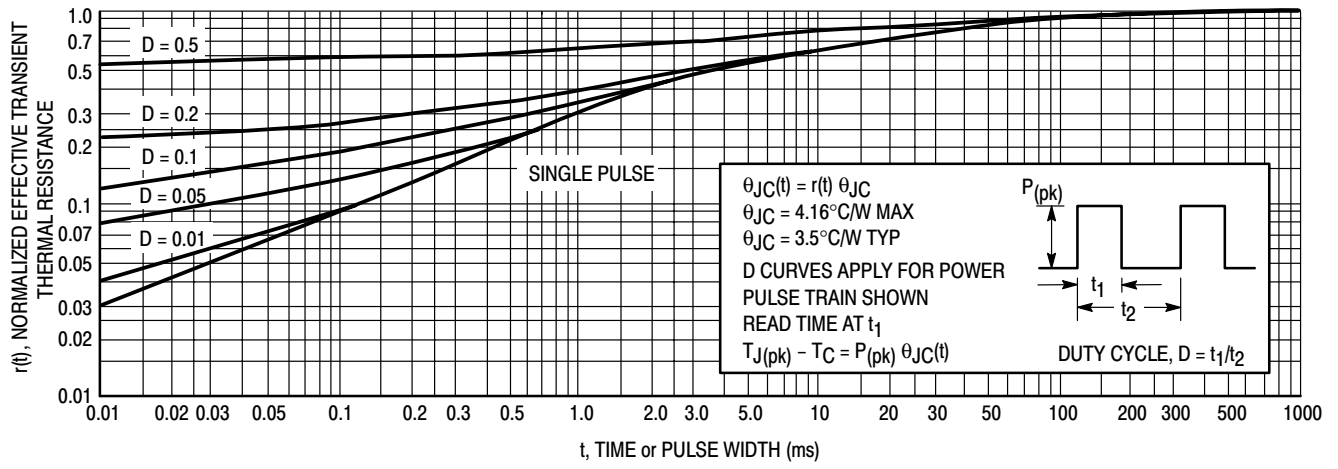


Figure 4. "On" Voltages

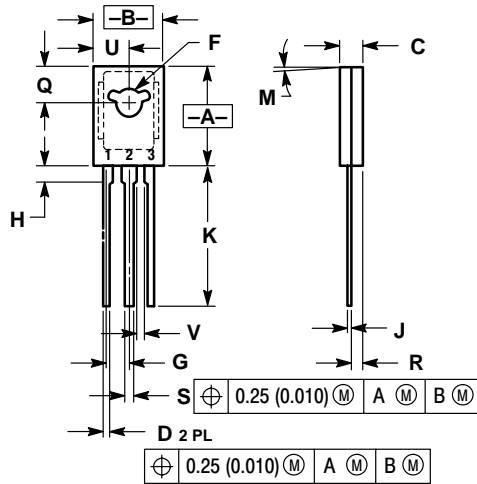
# BD179 BD179-10



# BD179 BD179-10

## PACKAGE DIMENSIONS


### TO-225AA CASE 77-09 ISSUE W



- NOTES:  
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	----	1.02	----

- STYLE 1:  
 PIN 1. EMITTER  
 2. COLLECTOR  
 3. BASE

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